

In The Claims

✓ Please cancel claims 1-30 without prejudice, and add new claims 31-53.

Sub B1
31. A layer comprising high purity tantalum, less than about 500 ppm, by weight, total metallic impurities, and less than about 50 ppm, by weight, tungsten or molybdenum.

A2
32. The layer of claim 31 wherein the layer is formed by sputter deposition.

Sub B2
33. A capacitor comprising high purity tantalum comprising tantalum, less than about 500 ppm, by weight, total metallic impurities, and less than about 50 ppm, by weight, tungsten or molybdenum.

34. The capacitor of claim 33 wherein the high purity tantalum is formed in the capacitor by sputter deposition.

35. A sputtering target blank comprising tantalum, less than 500 ppm by weight (ppmw) total metallic impurities, less than or equal to 50 ppmw molybdenum or tungsten, and less than about 100 ppmw oxygen.

36. The blank of claim 35 comprising less than 5 ppmw total of molybdenum and tungsten.

6 37. The blank of claim *4* 35 comprising less than 2 ppmw total of molybdenum and tungsten.

7 38. The blank of claim *4* 35 comprising less than 25 ppmw of oxygen.

8 36. The blank of claim ⁴35 comprising less than 10 ppb by weight (ppbw) each of uranium and thorium.

9 46. A sputtering target blank comprising tantalum, less than 500 ppmw total metallic impurities, less than 5 ppmw total of molybdenum and tungsten, less than about 100 ppmw oxygen, and less than or equal to 10 ppbw each of uranium and thorium.

10 41. A sputtering target blank comprising tantalum, less than 500 ppm by weight (ppmw) total metallic impurities, less than 2 ppmw total of molybdenum and tungsten, and less than 25 ppmw oxygen.

11 42. A sputtering target comprising the blank of claim ⁴35.

12 43. A sputtering target comprising the blank of claim ⁹46.

13 44. A sputtering target comprising the blank of claim ¹⁰41.

14 45. A material comprising tantalum, at least the tantalum being sputter deposited from the blank of claim ⁴35.

15 46. The material of claim ¹⁴45 consisting essentially of Ta metal, Ta₂O₅, or TaN.

16 47. A material comprising tantalum, at least the tantalum being sputter deposited from the blank of claim ⁹46.

17 48. The material of claim ¹⁶47 consisting essentially of Ta metal, Ta₂O₅, or TaN.

18 49. A material comprising tantalum, at least the tantalum being sputter deposited from the blank of claim ¹⁰41.

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The material of claim 49 consisting essentially of Ta metal, Ta₂O₅, or TaN.

51.

A capacitor comprising the material of claim 45.

52.

A capacitor comprising the material of claim 47.

53.

A capacitor comprising the material of claim 49.

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